



DMT10H009LFG

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D MAX</sub> T <sub>C</sub> = +25°C
100V	8.5mΩ @ V <sub>GS</sub> = 10V	50A
1000	12.5mΩ @ V <sub>GS</sub> = 4.5V	41A

#### Description

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

# Applications

- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

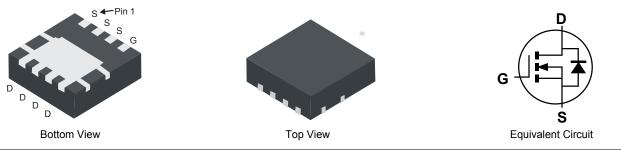
#### 100V N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features and Benefits**

- Low R<sub>DS(ON)</sub> Ensures On State Losses are Minimized
- Excellent Q<sub>gd x</sub> R<sub>DS (ON)</sub> Product (FOM)
- Advanced Technology for DC/DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

# **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.034 grams (Approximate)



#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMT10H009LFG-7	PowerDI3333-8	2,000/Tape & Reel
DMT10H009LFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website athttps://www.diodes.com/design/support/packaging/diodes-packaging/.

#### **Marking Information**



T09 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 20 = 2020) WW = Week Code (01 to 53)

and Lead-free.



# Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	100	V	
Gate-Source Voltage		V <sub>GSS</sub>	±20	V	
	T <sub>A</sub> = +25°C		13	А	
Continuous Drain Current (Note 5) $V_{GS}$ = 10V	T <sub>A</sub> = +70°C	ID	11		
	T <sub>C</sub> = +25°C		50	٨	
	T <sub>C</sub> = +70°C	ID	40	A	
Maximum Continuous Body Diode Forward Current (No	ote 5)	I <sub>S</sub>	25	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	200	А	
Pulsed Body Diode Continuous Current (10µs Pulse, Duty Cycle = 1%)		I <sub>SM</sub>	200	А	
Avalanche Current (L = 1mH)		I <sub>AS</sub>	17	А	
Avalanche Energy (L = 1mH)		E <sub>AS</sub>	144.5	mJ	

# Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	2	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ ext{ heta}JA}$	59	°C/W	
Total Power Dissipation	T <sub>C</sub> = +25°C	PD	30	W
Thermal Resistance, Junction to Case		R <sub>0JC</sub>	3.8	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

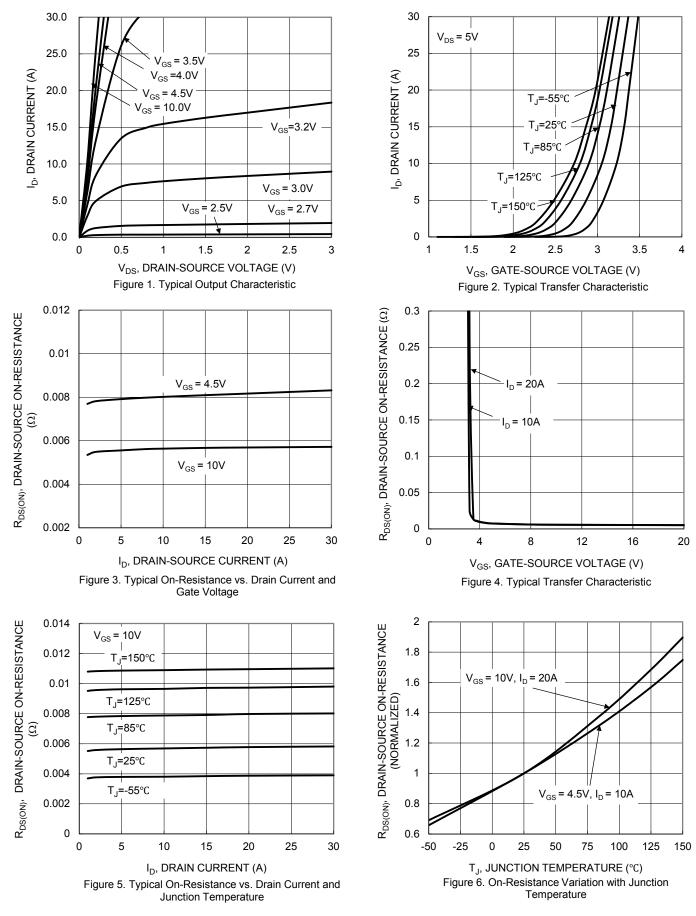
# Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)	Cymbol		. , , ,	max	Unit		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	—	1	μA	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	—	±100	nA	$V_{GS}$ = ±20V, $V_{DS}$ = 0V	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.1	_	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		—	6.4	8.5	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	8.2	12.5	11122	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 10A	
Diode Forward Voltage	V <sub>SD</sub>	_	0.8	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C <sub>iss</sub>	—	2361	_		V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V f = 1MHz	
Output Capacitance	Coss	—	611	-	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	16	_			
Gate Resistance	Rg	—	1.7	-	Ω	$V_{DS}$ = 0V, $V_{GS}$ = 0V, f = 1MHz	
Total Gate Charge	Qg	_	41	_			
Gate-Source Charge	Q <sub>gs</sub>	_	7.3	—	nC	V <sub>DD</sub> = 50V, I <sub>D</sub> = 13A, V <sub>GS</sub> = 10V	
Gate-Drain Charge	Q <sub>gd</sub>	_	9.3	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	7	—		$V_{DD}$ = 50V, $V_{GS}$ = 10V, $I_D$ = 13A, $R_g$ = 6 $\Omega$	
Turn-On Rise Time	t <sub>R</sub>		12	_	-		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	42	—	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	24	—	1	-	
Reverse Recovery Time	t <sub>RR</sub>	_	45	_	ns	1 - 120 $di/dt - 1000/ma$	
Reverse Recovery Charge	Q <sub>RR</sub>	_	68	_	nC	I <sub>F</sub> = 13A, di/dt = 100A/μs	

 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:

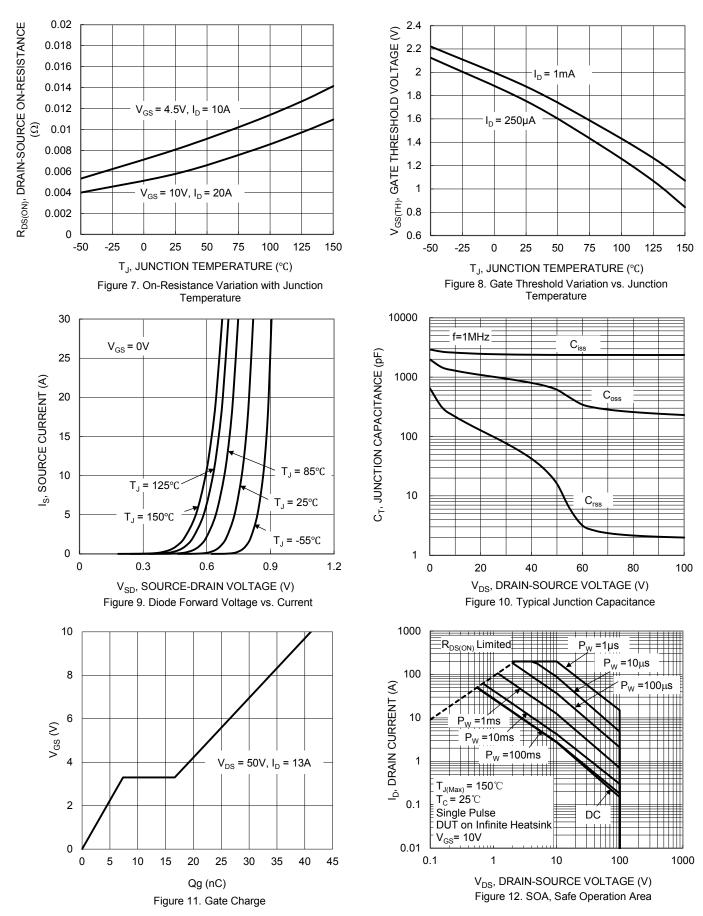


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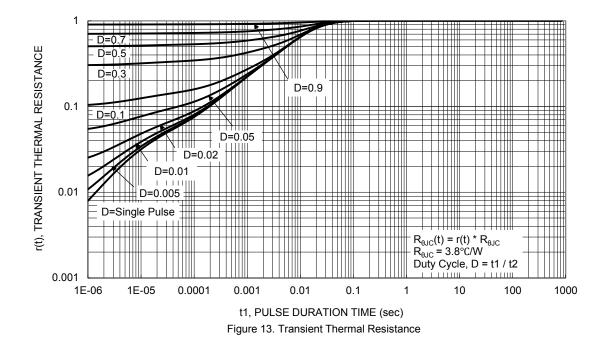


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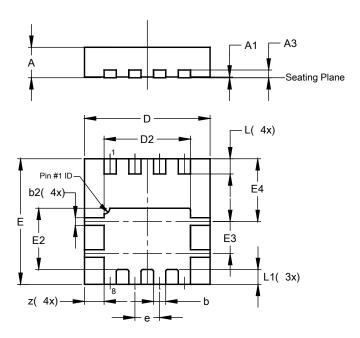






# Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

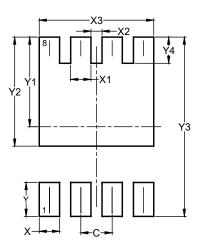


PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	-	-	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	_	_	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
z	_	_	0.515		
All I	All Dimensions in mm				

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

#### PowerDI3333-8



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